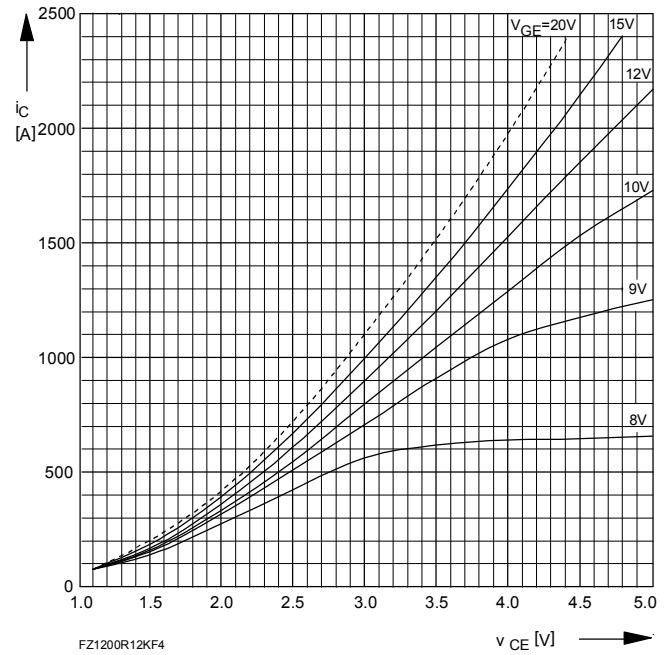
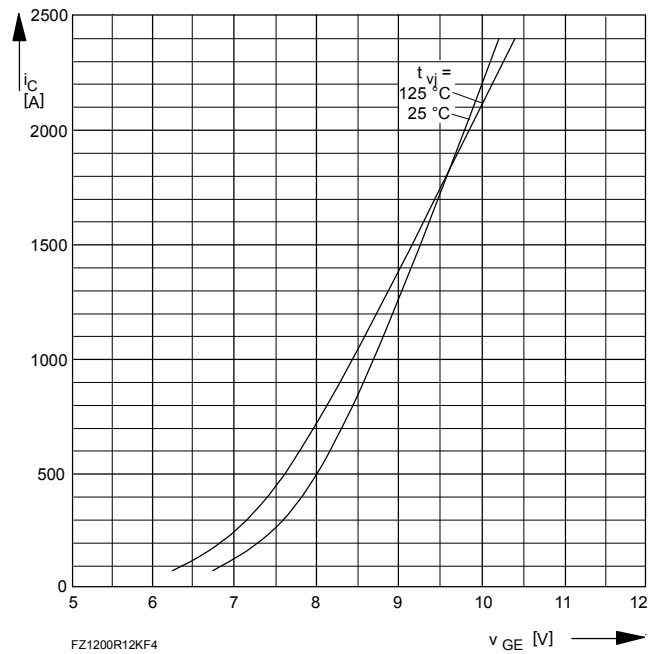


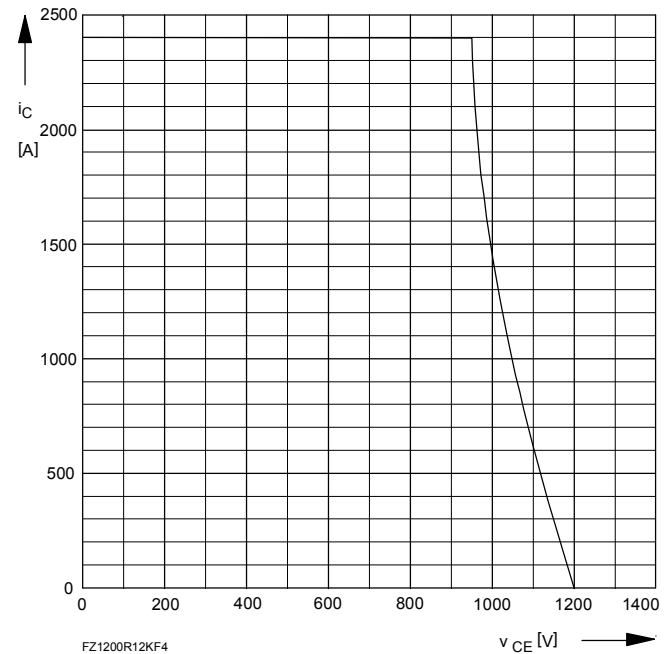
Bild/Fig. 1
 Kollektor-Emitter-Spannung im Sättigungsbereich (typisch)
 Collector-emitter-voltage in saturation region (typical)
 $V_{GE} = 15V$
 - - - $T_{vj} = 25^\circ C$
 — $T_{vj} = 125^\circ C$



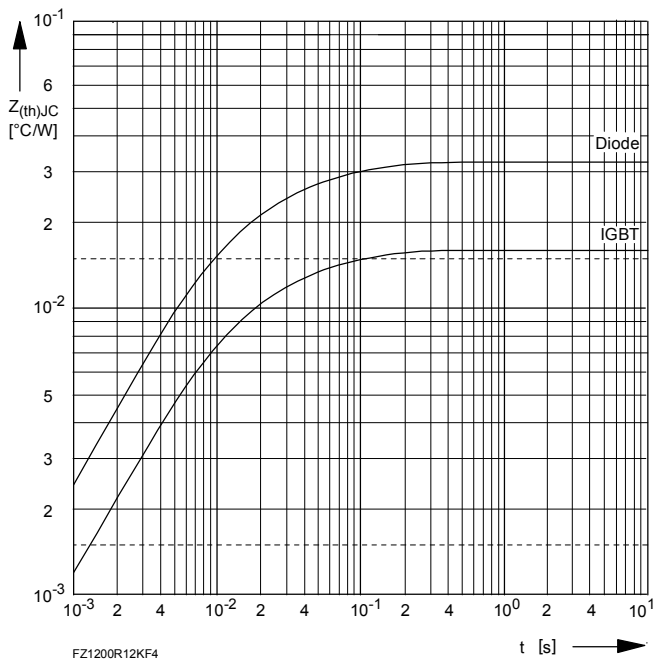
Bild/Fig. 2
 Kollektor-Emitter-Spannung im Sättigungsbereich (typisch)
 Collector-emitter-voltage in saturation region (typical)
 $T_{vj} = 125^\circ C$



Bild/Fig. 3
 Übertragungscharakteristik (typisch)
 Transfer characteristic (typical)
 $V_{CE} = 20V$

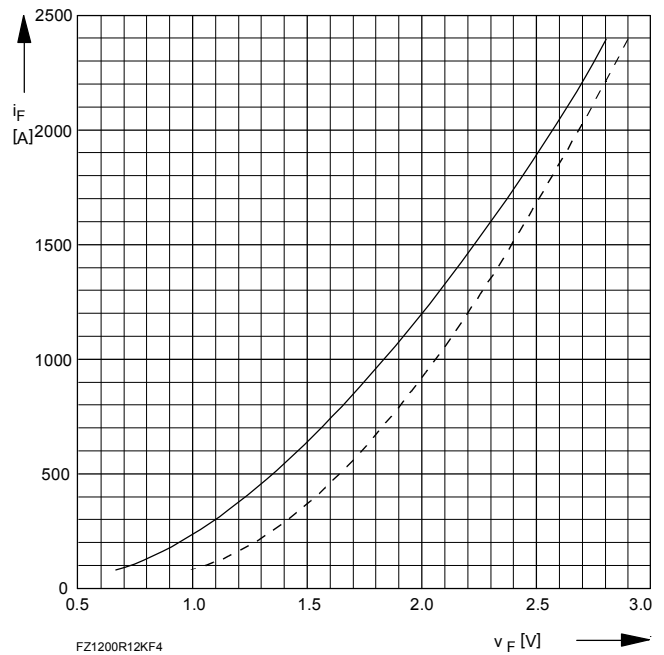


Bild/Fig. 4
 Rückwärts-Arbeitsbereich
 Reverse biased safe operating area
 $t_{vj} = 125^\circ C$, $v_{LE} = v_{LR} = 15V$, $R_G = 0,82W$



FZ1200R12KF4

Bild/Fig. 5
 Transienter innerer Wärmewiderstand (DC)
 Transient thermal impedance (DC)



FZ1200R12KF4

Bild/Fig. 6
 Durchlaßkennlinie der Inversdiode (typisch)
 Forward characteristic of the inverse diode (typical)
 $t_{vj} = 25^{\circ}C$
 — $t_{vj} = 125^{\circ}C$